

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims:

1 (currently amended). An IGBT with PN insulation, comprising:

a low-doped semiconductor substrate of a first conductivity type;

a low-doped drift zone of the first conductivity type formed in said low-doped semiconductor substrate; and

a first highly doped well zone of the first conductivity type and a second highly doped well zone of a second conductivity type, opposite to the first conductivity type, successively disposed between said drift zone and said semiconductor substrate providing an electrical PN insulation;

an IGBT cell connected to an anode, a cathode, and gate electrodes;

said substrate, said well zones and said IGBT cell forming a semiconductor body; and

said first well zone and said second well zone being
electrically separated from said anode, said cathode, and said
gate electrodes within said semiconductor body.

2 (currently amended). The IGBT according to claim 1, ~~which~~
~~comprises an IGBT cell with a cathode, and an~~ wherein said
IGBT cell is formed in said drift zone and said anode
surrounds ~~surrounding~~ said IGBT cell at a distance at an edge
of said drift zone, ~~formed in said drift zone.~~

3 (previously presented). The IGBT according to claim 1,
which comprises a short circuit strap connecting respective
two well zones on a surface thereof.

4 (previously presented). The IGBT according to claim 1,
which comprises a short-circuit strap connecting respective
two well zones and said semiconductor substrate to one another
on surfaces thereof.

5 (previously presented). A method of manufacturing a well
zone for an IGBT, which comprises manufacturing horizontal
regions of a well zone of an IGBT according to claim 1 by one
of implantation and diffusion, and manufacturing vertical
regions of the well zones by performing at least two epitaxial

steps with a subsequent process selected from the group consisting of implantation and diffusion.

6 (previously presented)). A method of manufacturing a well zone for the IGBT according to claim 1, which comprises manufacturing horizontal regions of a well zone of an IGBT according to claim 1 by one of implantation and diffusion, and manufacturing vertical regions of the well zones by etching trenches and subsequently filling the trenches with doped polycrystalline silicon and diffusing out.